

Description

The HXY5N10Al uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

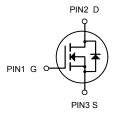


SOT-23

General Features

 $V_{DS} = 100V I_{D} = 5A$

 $R_{DS(ON)} < 125 m\Omega$ @ $V_{GS}=10V$



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID		Pack	Marking	Qty(PCS)
	HXY5N10AI	SOT-23	MA6	3000

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Symbol	Parameter	Parameter Rating	
VDS	Drain-Source Voltage	100	V
Vgs	Gate-Source Voltage ±20		V
I _D @T _A =25°C	C _A =25°C Continuous Drain Current, V _{GS} @ 10V¹ 5		Α
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.2	А
Ірм	Pulsed Drain Current ²	16	А
P _D @T _A =25°C	Total Power Dissipation ³	Total Power Dissipation ³ 3.1	
Тѕтс	Storage Temperature Range	Storage Temperature Range -55 to 150	
TJ	T _J Operating Junction Temperature Range -55 to 150		℃
RөJA	R _{θJA} Thermal Resistance Junction-ambient(steady state) ¹ 100		°C/W
R _θ JA	R _{0JA} Thermal Resistance Junction-ambient(t<10s) ¹		°C/W



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	100	108		V
Process	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =4A		110	125	mΩ
Rds(on)		V _{GS} =4.5V , I _D =2A		120	145	mΩ
V _G S(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250uA$	1.2	1.7	2.5	V
Ipss	Drain-Source Leakage Current	V _{DS} =80V , V _{GS} =0V , T _J =25°C			1	
IDSS		V _{DS} =80V , V _{GS} =0V , T _J =85°C			50	- uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.3	4.6	
Qg	Total Gate Charge (10V)			3.57		
Qgs	Gate-Source Charge	V _{DS} =30V , V _{GS} =10V , I _D =4A		0.76		nC
Qgd	Gate-Drain Charge			0.71		
Td(on)	Turn-On Delay Time			11		
Tr	Rise Time	V_{DD} =30V , V_{GS} =10V , R_{G} =3.3		6		ns
Td(off)	Turn-Off Delay Time	I _D =1A		30		
T _f	Fall Time			4		
Ciss	Input Capacitance			182		
Coss	Output Capacitance	V _{DS} =50V , V _{GS} =0V , f=1MHz		30		pF
Crss	Reverse Transfer Capacitance			3.6		
ls	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current			2	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

^{1.} The data tested by surface mounted on a 1 inch $^2\,\text{FR-4}$ board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C junction temperature

^{4.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

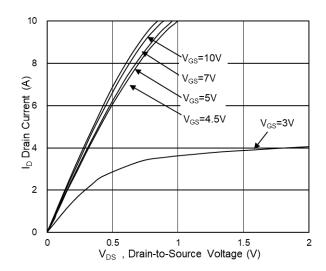


Fig.1 Typical Output Characteristics

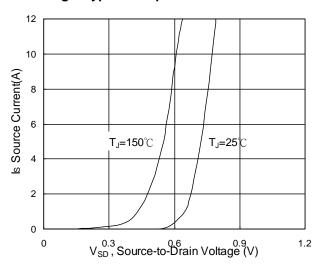


Fig.3 Source Drain Forward Characteristics

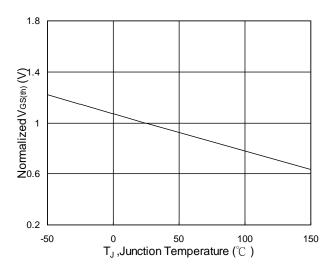


Fig.5 Normalized V_{GS(th)} vs T_J

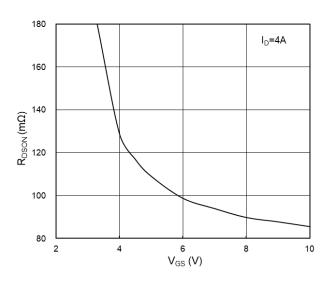


Fig.2 On-Resistance vs G-S Voltage

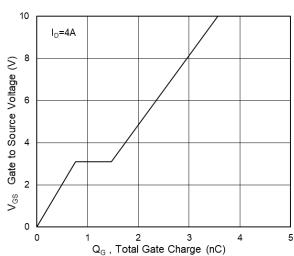


Fig.4 Gate-Charge Characteristics

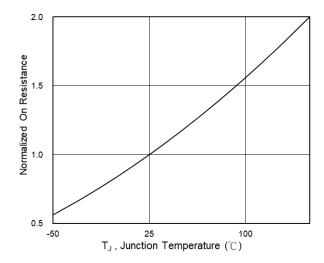
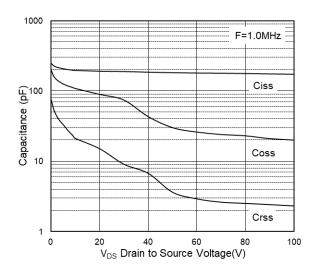


Fig.6 Normalized R_{DSON} vs T_J





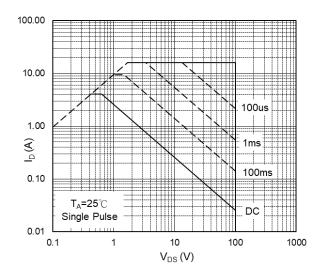


Fig.7 Capacitance

Fig.8 Safe Operating Area

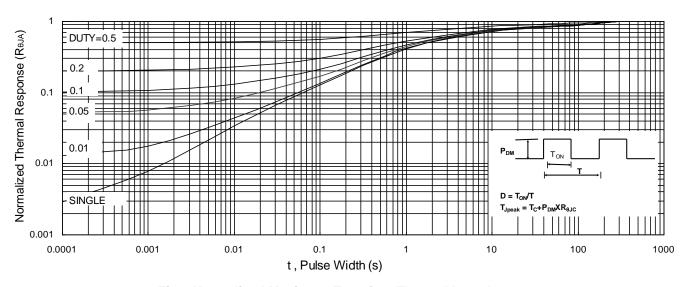


Fig.9 Normalized Maximum Transient Thermal Impedance

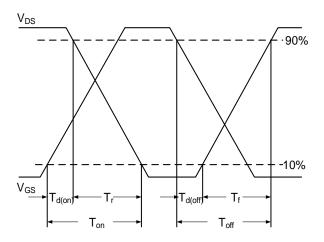


Fig.10 Switching Time Waveform

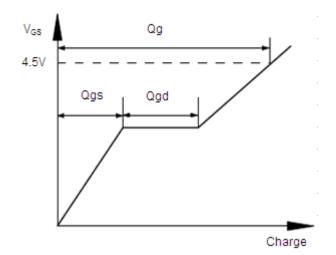
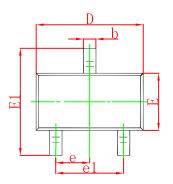
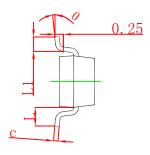


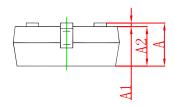
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

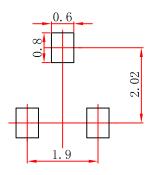






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

N-Channel Enhancement Mode MOSFET

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